

## Full - Bridge NPT IGBT Power Module





Pins 5/6/15/16 ; 3/4/17/18 ; 9/10 ; 11/12 must be shorted together

## $V_{CES} = 1200V$ $I_{C} = 25A$ @ Tc = 80°C

### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
    - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

### Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	40	
I <sub>C</sub>	Continuous Conector Current	$T_C = 80^{\circ}C$	25	Α
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
V <sub>GE</sub>	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	208	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	50A@1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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### Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ ; $V_{CE} = 1200V$				250	μΑ
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	2.5	3.2	3.7	V
V <sub>CE(sat)</sub>		$I_{\rm C} = 25 \text{A} \qquad \qquad T_{\rm j} = 125^{\circ} \text{C}$			4.0		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1 \text{mA}$		4		6	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

## Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			1650		
Coes	Output Capacitance				250		pF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz			110		
Qg	Total gate Charge	$V_{GE} = 15V$			160		
Q <sub>ge</sub>	Gate – Emitter Charge	$V_{Bus} = 600V$			10		nC
Q <sub>gc</sub>	Gate – Collector Charge	$I_{\rm C}=25{\rm A}$		70			
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch		60			
Tr	Rise Time	$V_{GE} = 15V$			50		ns
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 25A$			305		
$T_{\rm f}$	Fall Time	$R_G = 22\Omega$		30			
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (125°C)			60		
Tr	Rise Time	$V_{GE} = 15V$			50		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 25A$			346		ns
T <sub>f</sub>	Fall Time	$R_{\rm G} = 22\Omega$			40		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 600V$	$T_j = 125^{\circ}C$		3.5		. T
E <sub>off</sub>	Turn-off Switching Energy	$I_{C} = 25A$ $R_{G} = 22\Omega$	$T_j = 125^{\circ}C$		1.5		mJ
I <sub>sc</sub>	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 900V$ $t_p \le 10\mu s$ ; $T_i = 125^{\circ}C$			160		А
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.6	°C/W



#### Reverse diode ratings and characteristics (per diode)

	Characteristic	·	Test Conditions		Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage						V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V				100	μΑ
$I_F$	DC Forward Current		$Tc = 80^{\circ}C$		25		А
		$I_F = 25A$			2.6	3.1	v
$V_{\rm F}$	Diode Forward Voltage	$I_F = 50A$			3.2		
		$I_F = 25A$	$T_j = 125^{\circ}C$		1.8		
t			$T_j = 25^{\circ}C$	320			ns
۲r		$I_F = 25A$ $V_R = 667V$ $T_j = 125$	$T_{j} = 125^{\circ}C$		360		115
Qrr	Reverse Recovery Charge	$v_R = 00/v$ di/dt = 200A/µs	$T_j = 25^{\circ}C$		480		nC
			$T_{j} = 125^{\circ}C$		1800		nC
R <sub>thJC</sub>	Junction to Case Thermal Resistance					1.4	°C/W

### **Temperature sensor NTC**

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		22		kΩ
$\Delta R_{25}/R_{25}$	Resistance tolerance			5	%
$\Delta B/B$	Beta tolerance			3	/0
B 25/100	$T_{25} = 298.16 \text{ K}$		3980		K
	$R_{25}$				

$$R_T = \frac{R_{25}}{\exp\left[B_{25/100}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature  $R_T$ : Thermistor value at T

## Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range		-40		150		
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

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Package outline (dimensions in mm)



### **Typical Performance Curve**



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### Typical diode Performance Curve (per diode)





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